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Publisher Correction: Carrier lifetime enhancement in halide perovskite via remote epitaxy

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The original version of this Article contained an error in the author affiliations. The fifth affiliation incorrectly read ‘Beijing Advanced Innovation Center for Materials Genome Engineering, Institute for Advanced Materials and Technology, University of Science and Technology, Beijing 100083, China.’ The correct version reads ‘Beijing Advanced Innovation Center for Materials Genome Engineering, Institute for Advanced Materials and Technology, University of Science and Technology Beijing, Beijing 100083, China.’ This has now been corrected in both the PDF and HTML versions of the Article.

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